

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A semiconductor device, comprising an SRAM (Static Random Access Memory) including:

a semiconductor substrate

an access MOS (Metal Oxide Semiconductor) transistor formed on an active region bounded by an isolation region, wherein [[a]] an entire surface of the active region is entirely rounded so as to be inclined downward toward said isolation region; and

a driver MOS transistor.

2. (Cancelled)

3. (Original) The semiconductor device according to claim 1, wherein  
an isolation insulating film is formed in said isolation region,  
said isolation insulating film includes a bird's beak portion extending on said active region, and

said active region is covered with said bird's beak portion.

4. (Original) The semiconductor device according to claim 3, wherein said bird's beak portion has a larger thickness near said isolation region than in a center of said active region.

5. (Previously Presented) The semiconductor device according to claim 1, wherein said access MOS transistor has a smaller channel doping depth than that of said driver MOS transistor.

6. (Previously Presented) The semiconductor device according to claim 1, wherein a gate insulating film of said driver MOS transistor has a larger thickness than that of a gate insulating film of said driver MOS transistor.

Claims 7-11 (Canceled)